

L Number	Hits	Search Text	DB	Time stamp
2	767	(tft or thin adj film adj transistor) and etching near gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/26 10:34
3	271	polysilicon and ((tft or thin adj film adj transistor) and etching near gate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/26 10:34
4	53	thinning and ((tft or thin adj film adj transistor) and etching near gate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/26 10:39
5	12	("5164806" "5300804" "5600154" "5614728" "5789778" "5834352" "5874329" "6017781" "6066535" "6188058" "6198140" "6225644").PN.	USPAT	2004/05/26 10:36
6	4159	(thining or etching) near gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/26 10:40
7	767	((tft or thin adj film adj transistor) and etching near gate) and ((thining or etching) near gate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/26 10:40
8	243	cmos and (((tft or thin adj film adj transistor) and etching near gate) and ((thining or etching) near gate))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/26 10:40
9	162	(ldd or lightly adj doped adj drain) and (cmos and (((tft or thin adj film adj transistor) and etching near gate) and ((thining or etching) near gate)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/26 10:56
10	1	sacrificial adj gate and (cmos and (((tft or thin adj film adj transistor) and etching near gate) and ((thining or etching) near gate))-)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/26 10:56
11	16914	(ldd or lightly adj doped adj drain)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/26 10:56
12	243	sacrificial adj gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/26 10:56
13	72	((ldd or lightly adj doped adj drain)) and (sacrificial adj gate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/26 10:57